TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSIV)

# 2SK3565

## **Switching Regulator Applications**

Unit: mm

• Low drain-source ON resistance:  $R_{DS (ON)} = 2.0 \Omega (typ.)$ 

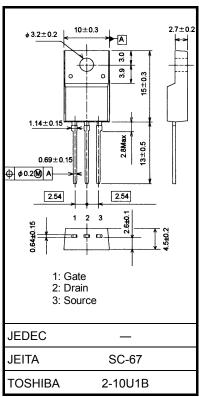
• High forward transfer admittance: |Y<sub>fS</sub>| = 4.5 S (typ.)

• Low leakage current:  $I_{DSS} = 100 \mu A (V_{DS} = 720 V)$ 

• Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

### Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	900	V	
Drain-gate voltage (F	$R_{GS} = 20 \text{ k}\Omega$ )	$V_{DGR}$	900	V	
Gate-source voltage		V <sub>GSS</sub>	±30	V	
Drain current	DC (Note 1)	ID	5	A	
	Pulse (t = 1 ms) (Note 1)	I <sub>DP</sub>	15		
Drain power dissipati	on (Tc = 25°C)	P <sub>D</sub>	45	W	
Single pulse avalanc	he energy (Note 2)	E <sub>AS</sub>	595	mJ	
Avalanche current		I <sub>AR</sub>	5	Α	
Repetitive avalanche	energy (Note 3)	E <sub>AR</sub>	4.5	mJ	
Channel temperature	)	T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	



Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

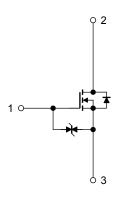
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	2.78	°C/W
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	62.5	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 90 \text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}(\text{Initial})$ , L = 43.6 mH,  $I_{AR} = 5.0 \text{ A}$ ,  $R_G = 25 \Omega$ 

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.



Start of commercial production 2002-06

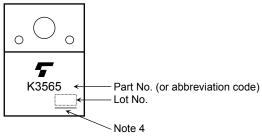
# **Electrical Characteristics (Ta = 25°C)**

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μΑ
Gate-source brea	akdown voltage	V (BR) GSS	$I_G = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$	±30	_	_	V
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 720 V, V <sub>GS</sub> = 0 V	_	_	100	μΑ
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	900	_	_	V
Gate threshold voltage		V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.0	_	4.0	V
Drain-source ON resistance		R <sub>DS</sub> (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3 A	_	2.0	2.5	Ω
Forward transfer admittance		Yfs	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 3 A	2.0	4.5	_	S
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	1150	_	pF
Reverse transfer capacitance		C <sub>rss</sub>			20		
Output capacitance		Coss		_	100	_	
Switching time	Rise time	t <sub>r</sub>	$\begin{array}{c c} 10 \text{ V} & \text{I}_{D} = 3 \text{ A} & \text{V}_{OUT} \\ \hline \text{VGS} & \text{OV} & \text{OV} & \text{OV} \\ \hline 50 \Omega & \text{S} & \text{RL} = \\ \hline \text{VDD} \approx 200 \text{ V} \end{array}$	_	30	_	
	Turn-on time	t <sub>on</sub>		_	70	_	20
	Fall time	t <sub>f</sub>			60		ns
	Turn-off time	t <sub>off</sub>	Duty $\leq$ 1%, $t_W = 10 \mu s$	_	170	_	
Total gate charge		Qg		_	28	_	
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \simeq 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}$	_	17	_	nC
Gate-drain charge		Q <sub>gd</sub>			11	_	

# Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	_	_	_	5	Α
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	_	_	_	15	Α
Forward voltage (diode)	V <sub>DSF</sub>	$I_{DR} = 5 A$ , $V_{GS} = 0 V$			-1.7	V
Reverse recovery time	t <sub>rr</sub>	$I_{DR} = 5 \text{ A}, V_{GS} = 0 \text{ V},$		900	_	ns
Reverse recovery charge	Qrr	dI <sub>DR</sub> /dt = 100 A/μs	_	5.4	_	μС

## Marking



Note 4: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

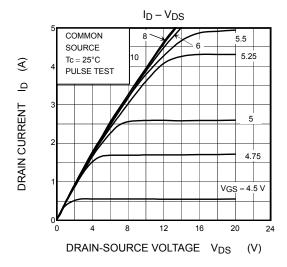
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

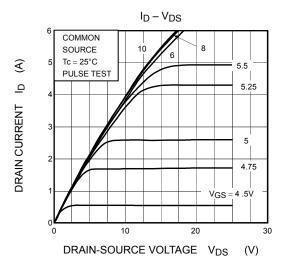
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

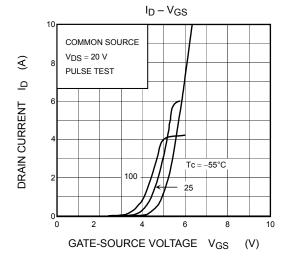
The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of Note 4

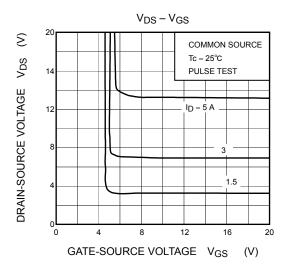
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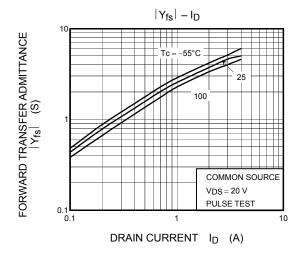
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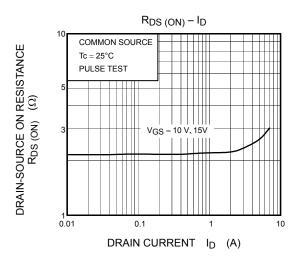




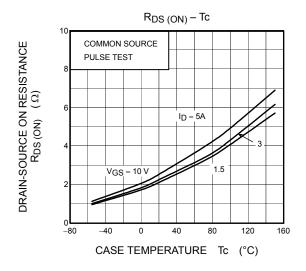


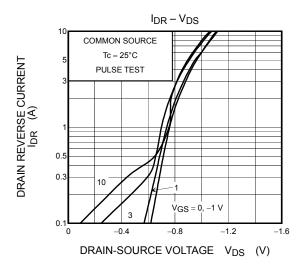


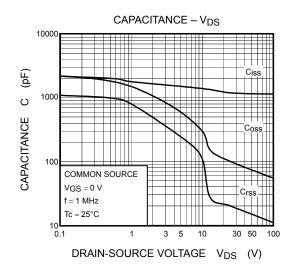


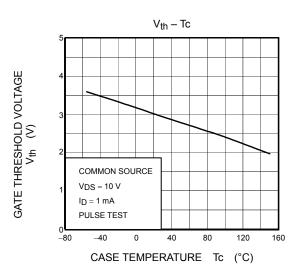


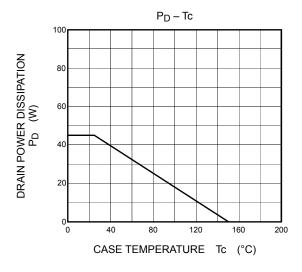
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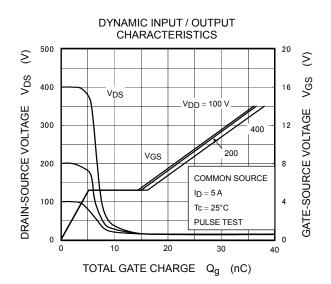


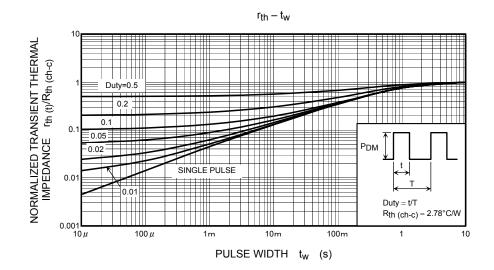


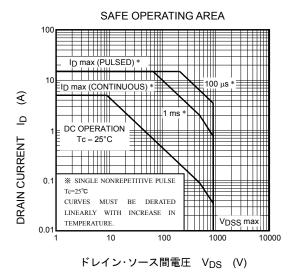


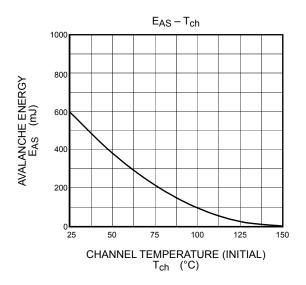


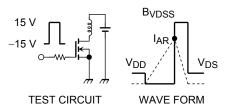












$$R_G = 25 \Omega$$

$$V_{DD} = 90 \text{ V, L} = 43.6 \text{mH}$$

$$E_{AS} = \frac{1}{2} \cdot \text{L} \cdot \text{I}^2 \cdot \left(\frac{\text{BVDSS}}{\text{BVDSS} - \text{VDD}}\right)$$

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